

PEMD24

50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k Ω , R2 = 100 k Ω

6 March 2023

Product data sheet

1. General description

NPN/PNP Resistor-Equipped double Transistor (RET) in an ultra small flat lead SOT666 Surface-Mounted Device (SMD) plastic package.

PNP/PNP complement: PEMB24

2. Features and benefits

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs

3. Applications

- Low current peripheral driver
- · Control of IC inputs
- · Replaces general-purpose transistors in digital applications

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
V _{CEO}	collector-emitter voltage	open base	[1]	-	-	50	V
Io	output current		[1]	-	=	20	mA
R1	bias resistor 1 (input)		[2]	70	100	130	kΩ
R2/R1	bias resistor ratio	T _{amb} = 25 °C	[2]	8.0	1	1.2	

- [1] For the PNP transistor with negative polarity.
- [2] See section "Test information" for resistor calculation and test conditions.



50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k Ω , R2 = 100 k Ω

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		O1 I2 GND2
2	I1	input (base) TR1	6 5 4	
3	O2	output (collector) TR2		R1 R2
4	GND2	GND (emitter) TR2		TR2
5	12	input (base) TR2	0	TR1 R2 R2
6	01	output (collector) TR1	1 2 3	
			SOT666	
				GND1 I1 O2 006aaa143

6. Ordering information

Table 3. Ordering information

Type number	e number Package					
	Name	Description	Version			
PEMD24	SOT666	plastic, surface-mounted package; 6 leads; 0.5 mm pitch; 1.6 mm x 1.2 mm x 0.55 mm body	<u>SOT666</u>			

7. Marking

Table 4. Marking codes

Type number	Marking code
PEMD24	6N

50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k Ω , R2 = 100 k Ω

8. Limiting values

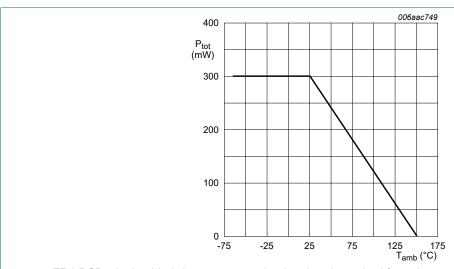
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transiste	or			•		
V _{CBO}	collector-base voltage	open emitter	[1]	-	50	V
V _{CEO}	collector-emitter voltage	open base	[1]	-	50	V
V _{EBO}	emitter-base voltage	open collector	[1]	-	10	V
VI	input voltage	input voltage TR1		-10	40	V
		input voltage TR2		-40	10	V
Io	output current		[1]	-	20	mA
I _{CM}	peak collector current		[1]	-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2]	-	200	mW
Per device	'		,	1		
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2]	-	300	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

^[1] For the PNP transistor with negative polarity.

^[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



FR4 PCB, single-sided, 35 μm copper, tin-plated and standard footprint

Fig. 1. Per device: Power derating curve

50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k Ω , R2 = 100 k Ω

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	625	K/W
Per device	Per device						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	416	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

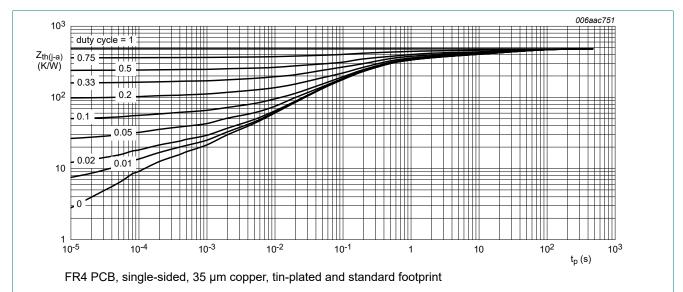


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k Ω , R2 = 100 k Ω

10. Characteristics

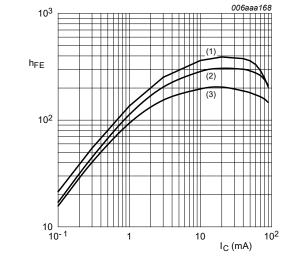
Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or						
V _{(BR)CBO}	collector-base breakdown voltage	$I_C = 100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$	[1]	50	-	-	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	$I_C = 2 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	50	-	-	V
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_{E} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	[1]	-	-	100	nA
I _{CEO}	collector-emitter cut-off	V _{CE} = 30 V; I _B = 0 A; T _{amb} = 25 °C	[1]	-	-	1	μΑ
	current	V _{CE} = 30 V; I _B = 0 A; T _{amb} = 150 °C	[1]	-	-	50	μA
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	[1]	-	-	50	μΑ
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 5 mA; T _{amb} = 25 °C	[1]	80	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 5 \text{ mA}; I_B = 0.25 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	-	-	150	mV
V _{I(off)}	off-state input voltage	V _{CE} = 5 V; I _C = 100 μA; T _{amb} = 25 °C	[1]	-	1.1	0.5	V
V _{I(on)}	on-state input voltage	V _{CE} = 0.3 V; I _C = 1 mA; T _{amb} = 25 °C	[1]	3	1.5	-	V
R1	bias resistor 1 (input)		[2]	70	100	130	kΩ
R2/R1	bias resistor ratio	T _{amb} = 25 °C	[2]	0.8	1	1.2	
TR1 (NPN)							
C _c	collector capacitance	V_{CB} = 10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C		-	-	2.5	pF
TR2 (PNP)							
C _c	collector capacitance	V_{CB} = -10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C		-	-	3	pF

^[1] For the PNP transistor with negative polarity.

^[2] See section "Test information" for resistor calculation and test conditions.

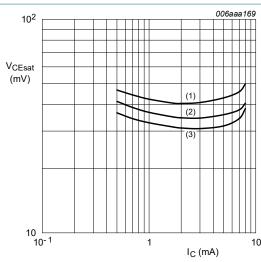
50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k Ω , R2 = 100 k Ω



 $V_{CE} = 5 V$ (1) $T_{amb} = 100 °C$

(2) T_{amb} = 25 °C (3) T_{amb} = -40 °C

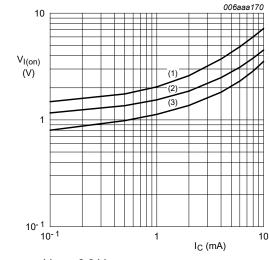
TR1 (NPN): DC current gain as a function of Fig. 3. collector current; typical values



 $I_{\rm C}/I_{\rm B}=20$

(1) T_{amb} = 100 °C (2) T_{amb} = 25 °C (3) T_{amb} = -40 °C

Fig. 4. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



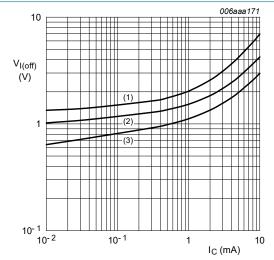
 V_{CE} = 0.3 V

(1) T_{amb} = -40 °C

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$





 $V_{CE} = 5 V$

(1) $T_{amb} = -40 \, ^{\circ}C$

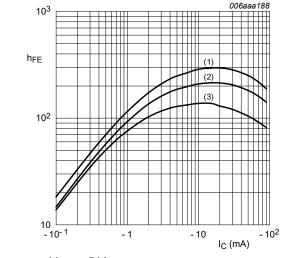
(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

TR1 (NPN): Off-state input voltage as a function of collector current; typical values

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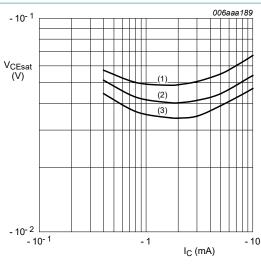
50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k Ω , R2 = 100 k Ω



(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

TR2 (PNP): DC current gain as a function of Fig. 7. collector current; typical values



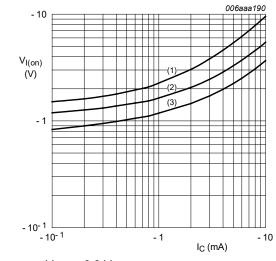
$$I_{\rm C}/I_{\rm B} = 20$$

$$I_{C}/I_{B} = 20$$
(1) $T_{amb} = 100 \, ^{\circ}C$
(2) $T_{amb} = 25 \, ^{\circ}C$
(3) $T_{amb} = -40 \, ^{\circ}C$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig. 8. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values



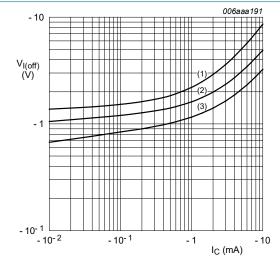
$$V_{CE} = -0.3 V$$

$$(1) T_{amb} = -40 °C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = 100 °C$$

Fig. 9. of collector current; typical values



$$V_{CE}$$
 = -5 V

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

TR2 (PNP): On-state input voltage as a function | Fig. 10. TR2 (PNP): Off-state input voltage as a function of collector current; typical values

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50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k Ω , R2 = 100 k Ω

11. Test information

Resistor calculation

• Calculation of bias resistor 1 (R1)

$$R_{I} = \frac{V(I_{2}) - V(I_{1})}{I_{2} - I_{1}}$$

· Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I3)}{R1 \cdot I3} - 1$$

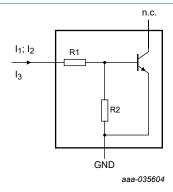


Fig. 11. TR1 (NPN): Resistor test circuit

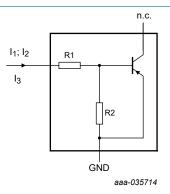


Fig. 12. TR2 (PNP): Resistor test circuit

Resistor test conditions

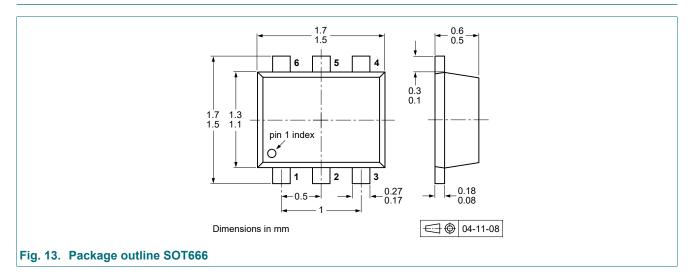
Table 8. Resistor test conditions

PEMD24	R1 (kΩ)	R2 (kΩ)	Test conditions		
			I ₁	l ₂	l ₃
TR1 (NPN)	100	100	20 μΑ	60 µA	-40 μΑ
TR2 (PNP)	100	100	-20 µA	-60 µA	40 μΑ

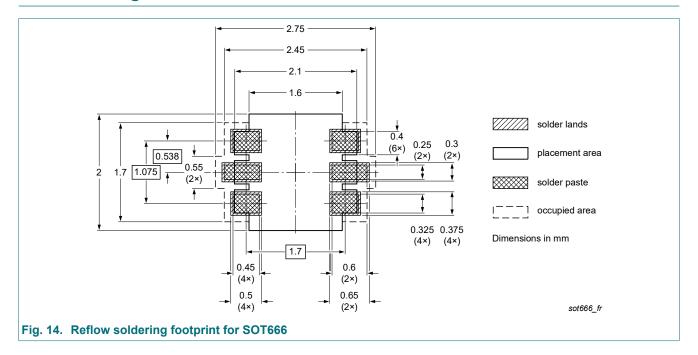
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50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k Ω , R2 = 100 k Ω

12. Package outline



13. Soldering



50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k Ω , R2 = 100 k Ω

14. Revision history

Table 9. Revision history

Table 6. Itevicion mote	• y			
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PEMD24 v.2	20230306	Product data sheet	-	PEMD24_PUMD24_1
Modifications:	Nexperia. Legal texts have bee Family data sheet sp Section "Packing info	ita sheet has been redesion adapted to the new constituted to single type data cormation" removed.	mpany name where approsheets.	, ,
PEMD24_PUMD24_1	20050502	Product data sheet	-	-

50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k Ω , R2 = 100 k Ω

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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